

3CD3,3CD4**PNP Silicon Low Frequency High Power Transistor****Features:**

1. Heavy output current.Small saturation voltage drop. Good temperature stability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for power amplify, Low-speed switch, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications							
			3CD3				3CD4			
			A	B	C	D	E	F	G	H
Collector-Emitter Voltage	V_{CEO}	V	30	50	80	110	150	200	250	300
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	30	50	80	110	150	200	250	300
Emitter-Base Voltage	V_{EBO}	V	3				4			
Max. Collector Current	I_{CM}	A	1				2			
Max. Collector Dissipation	P_{CM}	W	10 ($T_c \leq 75^\circ C$)				20 ($T_c \leq 75^\circ C$)			
Junction Temperature	T_{jm}	$^\circ C$	175							
Storage Temperature	T_{stg}	$^\circ C$	-55~+175							
Collector-Emitter Leakage Current	I_{CEO}	mA	2 ($V_{CE}=20V$)							
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.5 (A~E: $I_C=0.5A, I_B=0.1A$; F~H: $I_C=0.2A, I_B=0.04A$)				1.5 (A~E: $I_C=1A, I_B=0.2A$; F~H: $I_C=0.5A, I_B=0.1A$)			
DC Current Gain	h_{FE}		Max.:240, Min.:15 (A~E: $V_{CE}=10V, I_C=0.5A$; F~H: $V_{CE}=10V, I_C=0.2A$)				Max.:240, Min.:15 (A~E: $V_{CE}=10V, I_C=1.0A$; F~H: $V_{CE}=10V, I_C=0.5A$)			
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥ 3 ($I_E=3mA$)				≥ 4 ($I_E=2mA$)			

 h_{FE} Colored:

Color	Red	Orange	Yellow	Green	Blue	Purple
h_{FE}	15~25	25~40	40~55	55~80	80~120	120~240

Outline and Dimensions: